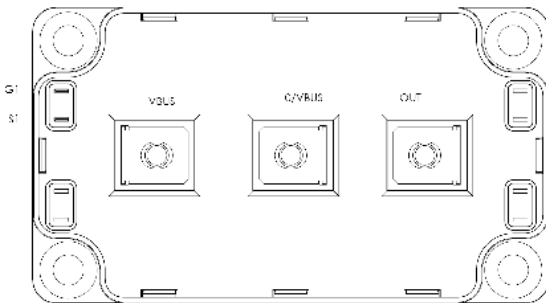
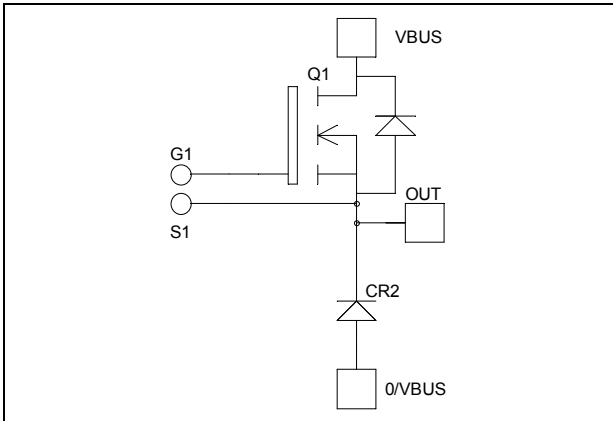


## Buck chopper MOSFET Power Module

$V_{DSS} = 200V$   
 $R_{DSon} = 4m\Omega \text{ typ @ } T_j = 25^\circ C$   
 $I_D = 372A \text{ @ } T_c = 25^\circ C$



### Application

- AC and DC motor control
- Switched Mode Power Supplies

### Features

- Power MOS 7<sup>®</sup> MOSFETs
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	200	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	372
		$T_c = 80^\circ C$	278
$I_{DM}$	Pulsed Drain current	1488	A
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	5	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	1250
$I_{AR}$	Avalanche current (repetitive and non repetitive)	100	A
$E_{AR}$	Repetitive Avalanche Energy	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy	3000	

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 200V			500	μA
		T <sub>j</sub> = 25°C				
		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 160V			2000	
R <sub>DS(on)</sub>	Drain – Source on Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 186A		4	5	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 10mA	3		5	V
I <sub>GSS</sub>	Gate – Source Leakage Current	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0V			±200	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0V		28.9		nF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 25V		9.32		
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1MHz		0.58		
Q <sub>g</sub>	Total gate Charge	V <sub>GS</sub> = 10V		560		nC
Q <sub>gs</sub>	Gate – Source Charge	V <sub>Bus</sub> = 100V		212		
Q <sub>gd</sub>	Gate – Drain Charge	I <sub>D</sub> = 372A		268		
T <sub>d(on)</sub>	Turn-on Delay Time	<b>Inductive switching @ 125°C</b>		32		ns
T <sub>r</sub>	Rise Time	V <sub>GS</sub> = 15V		64		
T <sub>d(off)</sub>	Turn-off Delay Time	V <sub>Bus</sub> = 133V		88		
T <sub>f</sub>	Fall Time	I <sub>D</sub> = 372A R <sub>G</sub> = 1.2Ω		116		
E <sub>on</sub>	Turn-on Switching Energy	<b>Inductive switching @ 25°C</b>		3396		μJ
E <sub>off</sub>	Turn-off Switching Energy	V <sub>GS</sub> = 15V, V <sub>Bus</sub> = 133V I <sub>D</sub> = 372A, R <sub>G</sub> = 1.2Ω		3716		
E <sub>on</sub>	Turn-on Switching Energy	<b>Inductive switching @ 125°C</b>		3744		μJ
E <sub>off</sub>	Turn-off Switching Energy	V <sub>GS</sub> = 15V, V <sub>Bus</sub> = 133V I <sub>D</sub> = 372A, R <sub>G</sub> = 1.2Ω		3944		

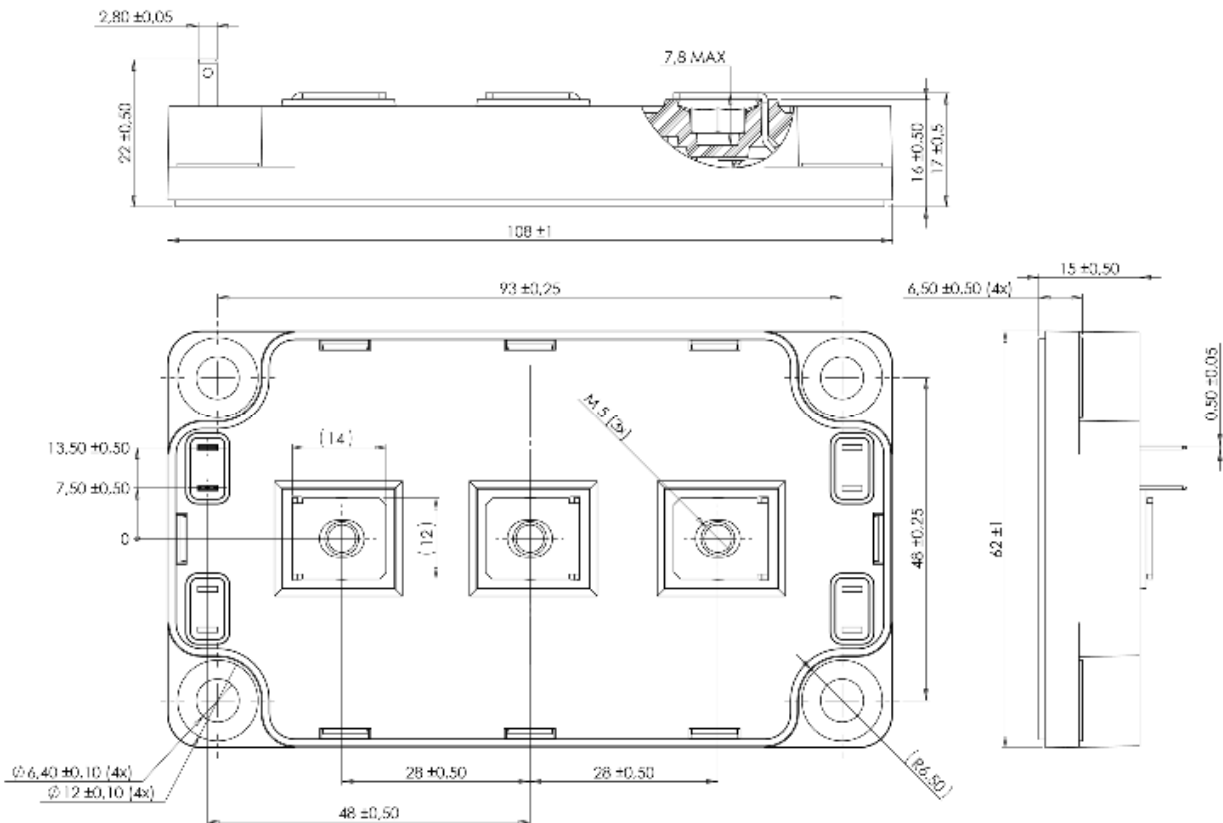
**Chopper diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage		200			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> = 200V			250	μA
		T <sub>j</sub> = 25°C				
		T <sub>j</sub> = 125°C			750	
I <sub>F</sub>	DC Forward Current	T <sub>c</sub> = 80°C		300		A
V <sub>F</sub>	Diode Forward Voltage	I <sub>F</sub> = 300A		1	1.1	V
		I <sub>F</sub> = 600A		1.4		
		I <sub>F</sub> = 300A	T <sub>j</sub> = 125°C		0.9	
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 300A	T <sub>j</sub> = 25°C		60	ns
		V <sub>R</sub> = 133V	T <sub>j</sub> = 125°C		110	
Q <sub>rr</sub>	Reverse Recovery Charge	di/dt = 600A/μs	T <sub>j</sub> = 25°C		600	nC
			T <sub>j</sub> = 125°C		2520	

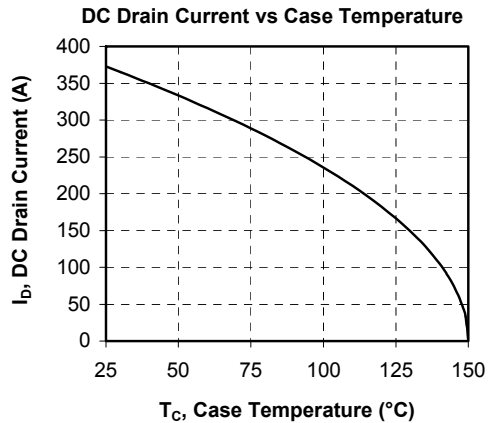
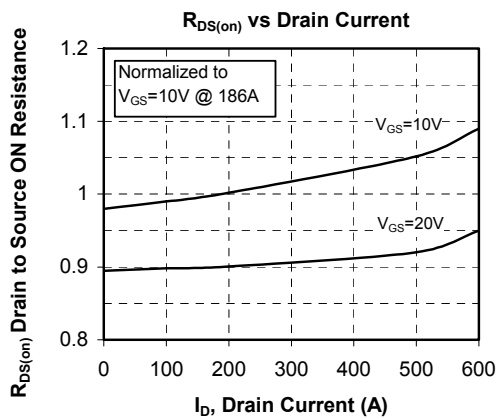
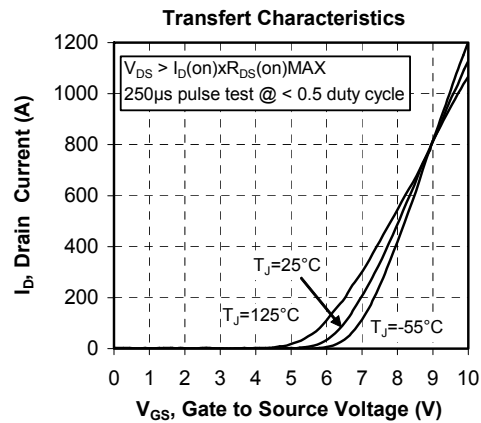
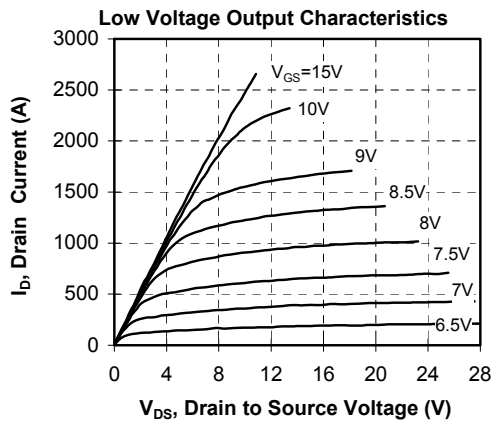
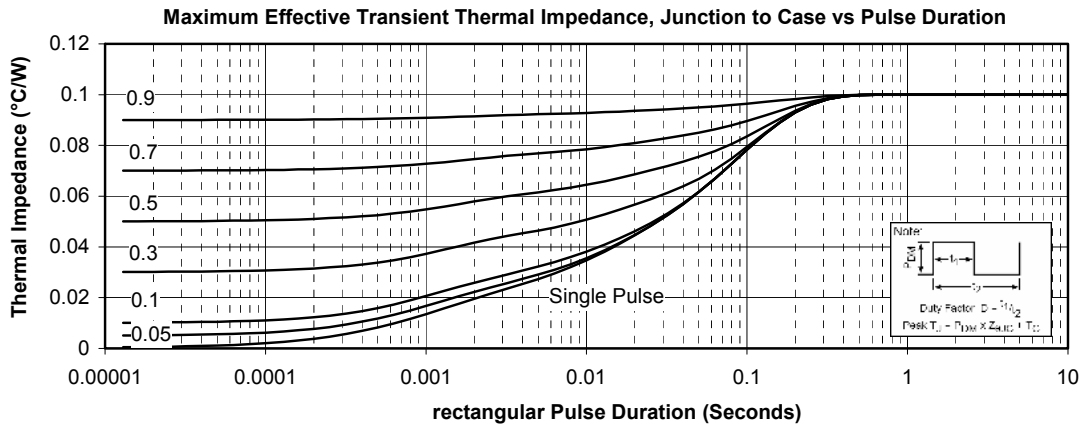
## Thermal and package characteristics

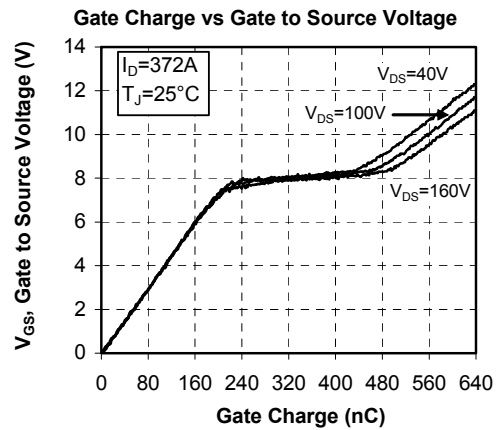
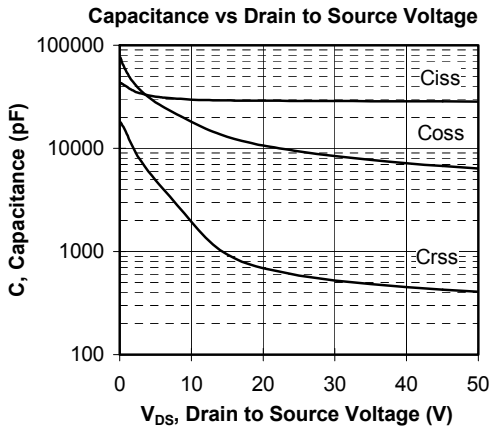
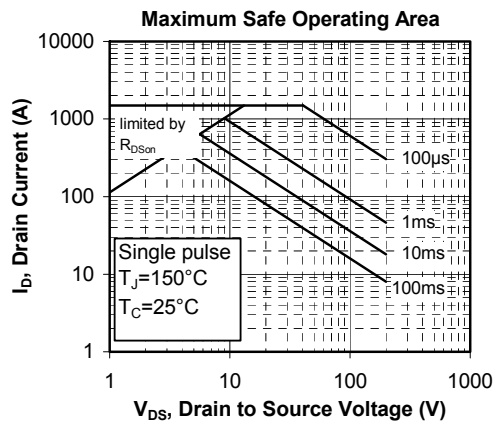
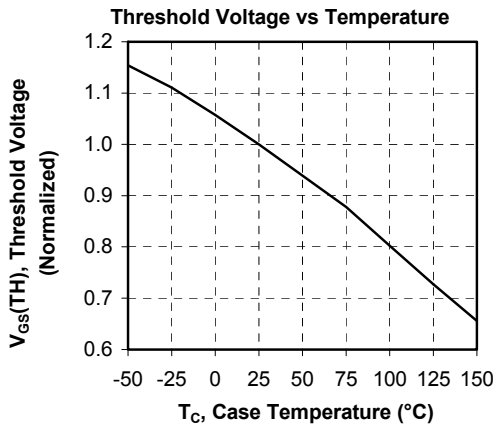
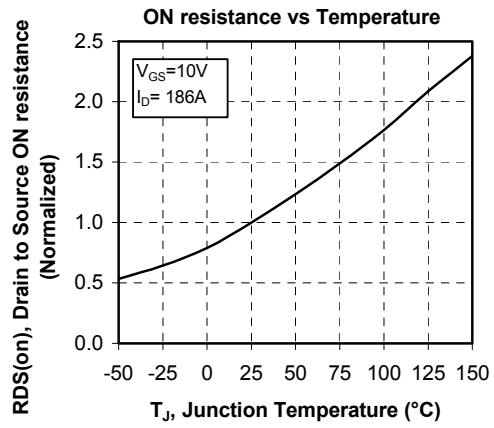
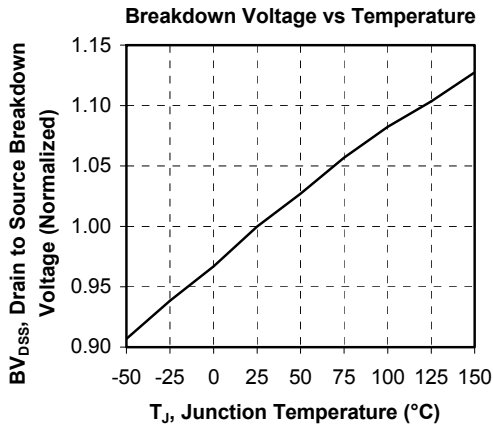
Symbol	Characteristic		Min	Typ	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance	Transistor			0.1	°C/W
		Diode			0.2	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz		4000			V
T <sub>J</sub>	Operating junction temperature range		-40		150	°C
T <sub>STG</sub>	Storage Temperature Range		-40		125	
T <sub>C</sub>	Operating Case Temperature		-40		100	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package Weight				300	g

## SP6 Package outline (dimensions in mm)

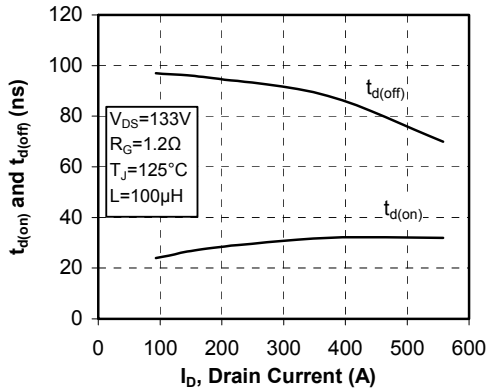


See application note APT0601 - Mounting Instructions for SP6 Power Modules on [www.microsemi.com](http://www.microsemi.com)

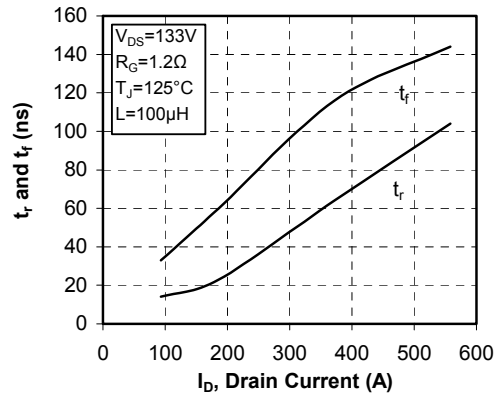
**Typical Performance Curve**




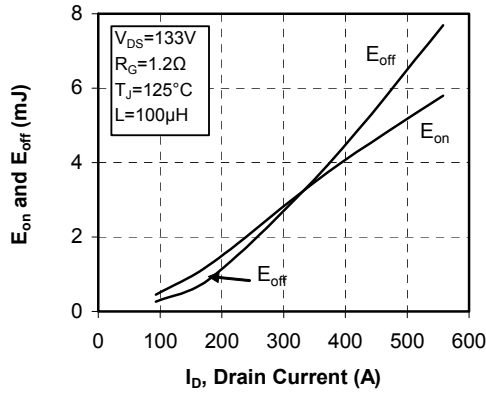
**Delay Times vs Current**



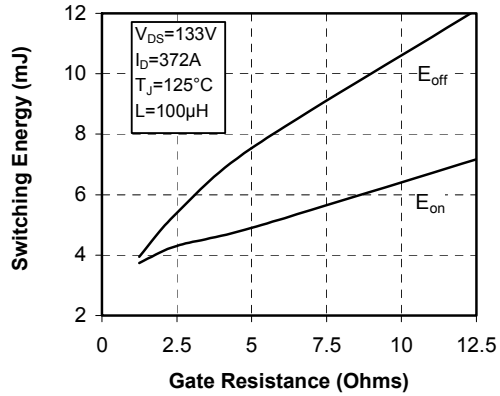
**Rise and Fall times vs Current**



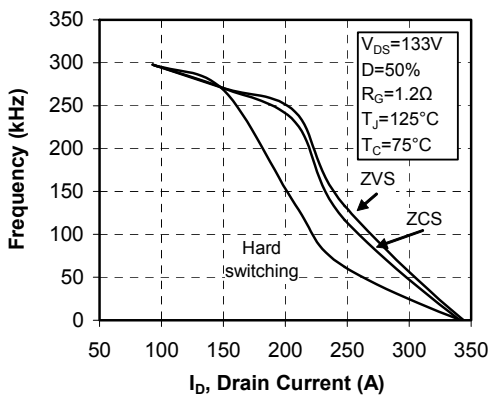
**Switching Energy vs Current**



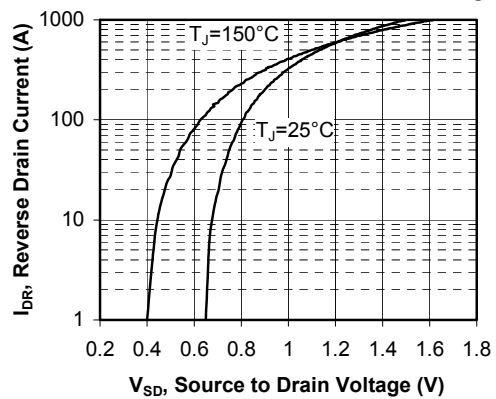
**Switching Energy vs Gate Resistance**



**Operating Frequency vs Drain Current**



**Source to Drain Diode Forward Voltage**



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